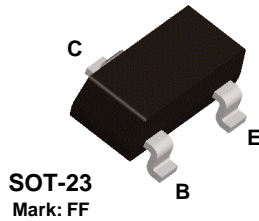


BCV27



NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current - Continuous	1.2	A
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BCV27	
P_D	Total Device Dissipation Derate above 25°C	350	mW
		2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

NPN Darlington Transistor

(continued)

BCV27

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	30			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ }\mu\text{A}, I_E = 0$	40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100 \text{ nA}, I_C = 0$	10			V
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$			0.1	μA
I_{EBO}	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, I_C = 0$			0.1	μA

ON CHARACTERISTICS

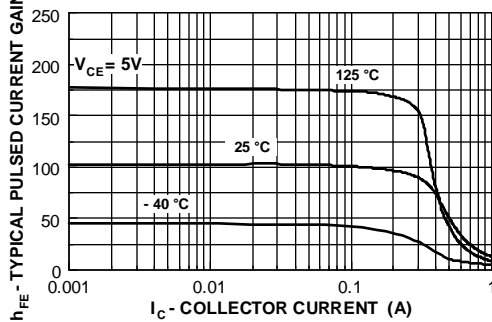
h_{FE}	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	4,000 10,000 20,000			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$			1.5	V

SMALL SIGNAL CHARACTERISTICS

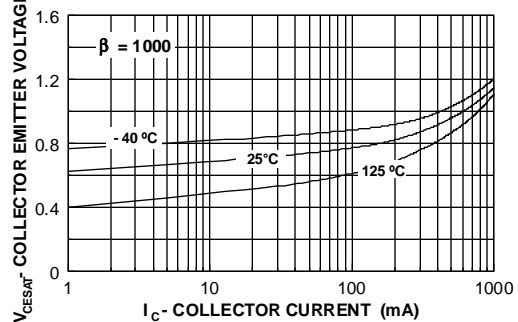
f_T	Current Gain - Bandwidth Product	$I_C = 30 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 100 \text{ MHz}$		220		MHz
C_C	Collector Capacitance	$V_{CB} = 30 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		3.5		pF

Typical Characteristics

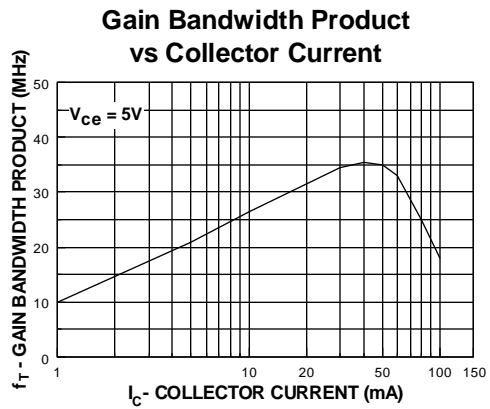
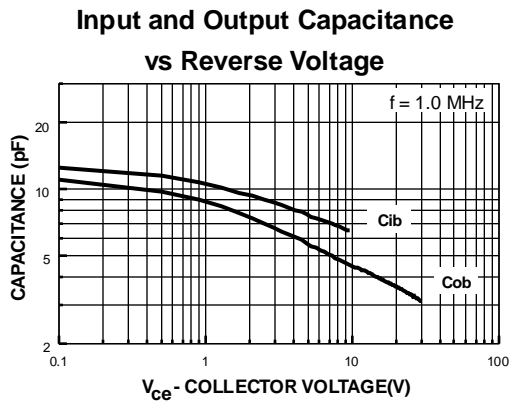
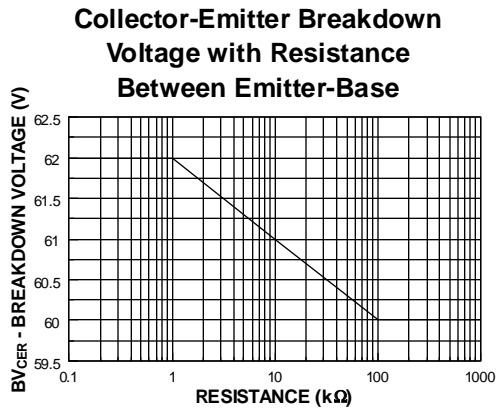
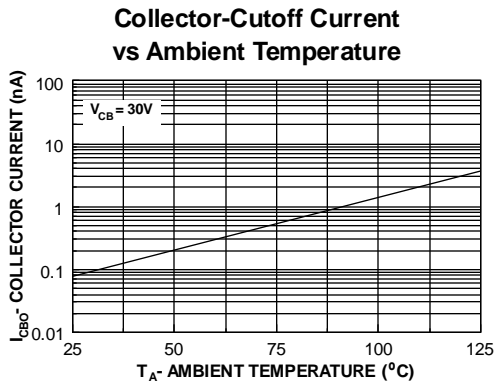
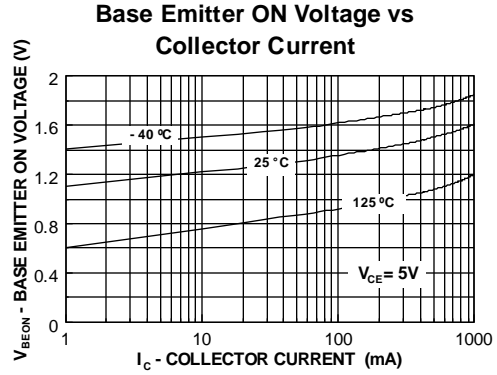
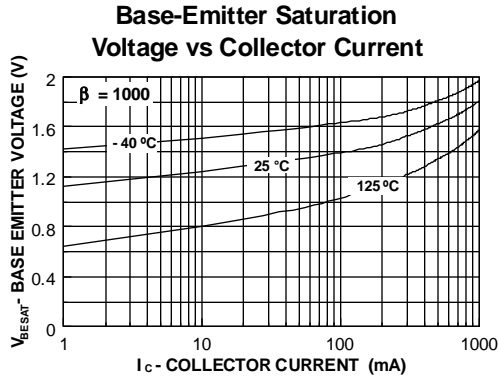
Typical Pulsed Current Gain vs Collector Current



Collector-Emitter Saturation Voltage vs Collector Current



Typical Characteristics (continued)



Typical Characteristics (continued)

